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PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM 10085903	FILING DATE 02 28 2002	CLASS 257	SUBCLASS	GAU 2875	EXAMINER
**APPLICANTS: Wei Andy, Sultan Akif, Wu David					
**CONTINUING DATA VERIFIED:					
** FOREIGN APPLICATIONS VERIFIED:					
PG-PUB		DO NOT PUBLISH <input type="checkbox"/>		RESCIND <input type="checkbox"/>	
Foreign priority claimed		<input type="checkbox"/> yes <input type="checkbox"/> no		ATTORNEY DOCKET NO	
35 USC 119 conditions met		<input type="checkbox"/> yes <input type="checkbox"/> no		AMDI 115 HON	
Verified and Acknowledged Examination					
TITLE : SOI mosfet junction degradation using multiple buried amorphous layers					

NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Total Claims	Print Claim for O.G
ISSUE FEE		DRAWING	
Amount Due	Date Paid	Sheets Drwg.	Figs. Drwg. Print Fig.
<input type="checkbox"/> TERMINAL DISCLAIMER		Application Examiner	
		PREPARED FOR ISSUE	
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